

RELIABILITY MONITOR

PRODUCT	MONITOR DATE	DATE CODE	ASSEMBLY FACILITY	ASSEMBLY LOT NO	PROCESS TYPE	PACKAGE TYPE
DS1669	May-97	9706 B3	OMEDATA	DD642765ABA1	1.2μ OX/NI EEPROM	08 SOIC 208

STRESS/JOB NO.

**READPOINT
(Sample Size/No. of Fails)**

Preconditioning (P/C):
HTC Vapor Phase
P-19656

<u>Electrical</u>	<u>Cum %</u>
235/0	0.0%

Infant / High Voltage Life **
125°C, 7.0 V.
P-19807, P-19831

<u>48 Hr</u>	<u>336 Hr</u>	<u>1KHr</u>	<u>*Failure Rate</u>
227/0	77/0		

*Chi Squared Method, 60% C. L., 55°C & 5.5V; Temperature Derating: Ea = 0.7 ev; Voltage Derating B = 1.0
** with Write Cycle Program stress = 60~/hr/cell

Temp Cycle
-55°C to +125°C
P-19832

<u>300 ~</u>	<u>1K ~</u>	<u>Cum %</u>
36/0		

Biased Moisture
85°C/85% RH, 5.5 V.
P-19833

<u>274 Hr</u>	<u>959 Hr</u>	<u>Cum %</u>
75/0		

Storage Life
150°C, No bias
P-19834

<u>0 Hr</u>	<u>336 Hr</u>	<u>1KHr</u>	<u>Cum %</u>
38/0	38/1		
Write Data	F1		

Failure Mode

F1: Read EEPROM

Failure Analysis

In process